

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC792

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For voltage regulator, inverter, switching mode power supply applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

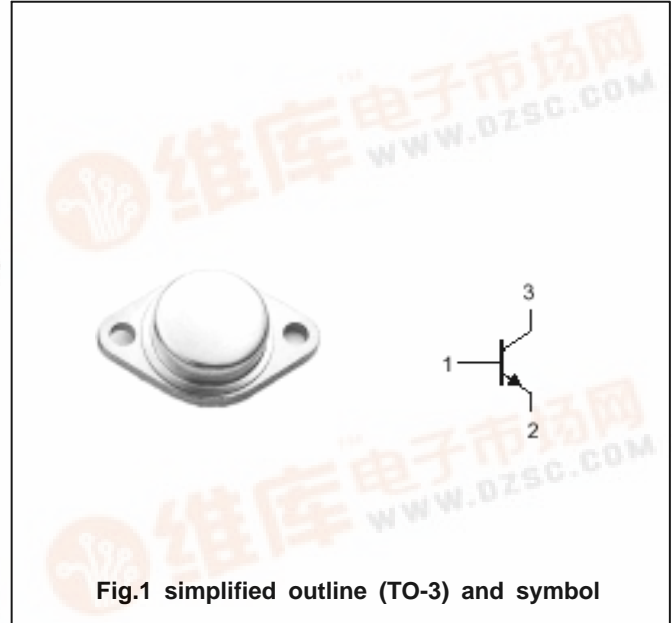


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	400	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1.5	A
P _C	Collector power dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.3A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1.5A; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =300V; I _E =0			50	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			50	μ A
h _{FE}	DC current gain	I _C =0.3A ; V _{CE} =10V	30		200	
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V		10		MHz

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PACKAGE OUTLINE

